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ABSTRACT

A copper alloy sputtering target most suitable for formation of an interconnection material of a semiconductor device, particularly for formation of a seed layer, characterized in that the target contains 0.4 to 5wt% of Sn, and the structure of the target does not substantially contain any precipitates, and the resistivity of the target material is $2.2 \mu \Omega \text{cm}$ or more. This target enables formation of an interconnection material of a semiconductor device, particularly a uniform seed layer stable during copper electroplating and is excellent in sputtering deposition characteristics. A method for manufacturing such a target is also disclosed.